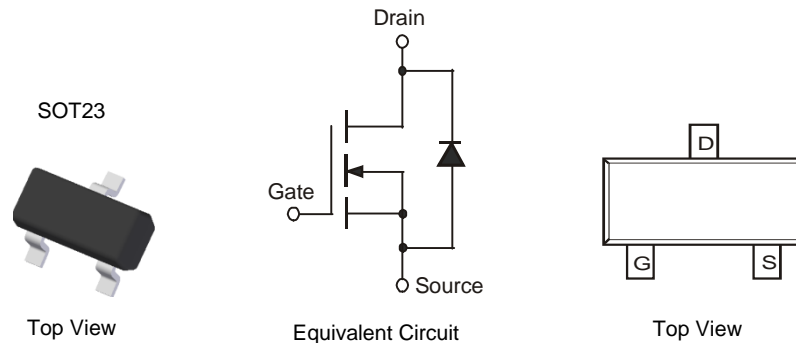


## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

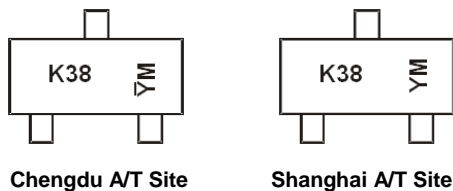


## Ordering Information (Note 5)

| Part Number | Qualification | Case  | Packaging         |
|-------------|---------------|-------|-------------------|
| BSS138-7-F  | Commercial    | SOT23 | 3000/Tape & Reel  |
| BSS138-13-F | Commercial    | SOT23 | 10000/Tape & Reel |
| BSS138Q-7-F | Automotive    | SOT23 | 3000/Tape & Reel  |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



K38 = Product Type Marking Code  
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site)  
 ȲM = Date Code Marking for CAT (Chengdu Assembly/ Test Site)  
 Y or Ȳ = Year (ex: E = 2017)  
 M = Month (ex: 9 = September)

### Date Code Key

| Year | 1998 | 1999 | 2000 | ... | 2002 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 |
|------|------|------|------|-----|------|------|------|------|------|------|------|------|------|------|------|
| Code | J    | K    | L    | ... | N    | D    | E    | F    | G    | H    | I    | J    | K    | L    | M    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                    | Symbol           | Value | Unit |
|---|------------------|-------|------|
| Drain-Source Voltage                              | V <sub>DSS</sub> | 50    | V    |
| Drain-Gate Voltage R <sub>GS</sub> ≤ 20KΩ         | V <sub>DGR</sub> | 50    | V    |
| Gate-Source Voltage                               | V <sub>GSS</sub> | ±20   | V    |
| Gate-Source Voltage                               |                  | ±40   | V    |
| Drain Current                                     | I <sub>D</sub>   | 200   | mA   |
| Pulsed Drain Current (10μs Pulse Duty Cycle = 1%) | I <sub>DM</sub>  | 1     | A    |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 6)                       | P <sub>D</sub>                    | 300         | mW   |
| Thermal Resistance, Junction to Ambient (Note 6) | R <sub>θJA</sub>                  | 417         | °C/W |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                      | Symbol              | Min | Typ | Max  | Unit | Test Condition   |
|-------------------------------------|---------------------|-----|-----|------|------|--|
| <b>OFF CHARACTERISTICS (Note 7)</b> |                     |     |     |      |      |  |
| Drain-Source Breakdown Voltage      | BV <sub>DSS</sub>   | 50  | 75  | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                         |
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>    | —   | —   | 0.5  | μA   | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V                          |
| Gate-Body Leakage                   | I <sub>GSS</sub>    | —   | —   | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                         |
| <b>ON CHARACTERISTICS (Note 7)</b>  |                     |     |     |      |      |  |
| Gate Threshold Voltage              | V <sub>GS(TH)</sub> | 0.5 | 1.2 | 1.5  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA           |
| Static Drain-Source On-Resistance   | R <sub>DS(ON)</sub> | —   | 1.4 | 3.5  | Ω    | V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.22A                        |
| Forward Transconductance            | g <sub>FS</sub>     | 100 | —   | —    | mS   | V <sub>DS</sub> = 25V, I <sub>D</sub> = 0.2A, f = 1.0KHz             |
| <b>DYNAMIC CHARACTERISTICS</b>      |                     |     |     |      |      |  |
| Input Capacitance                   | C <sub>iss</sub>    | —   | —   | 50   | pF   | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz              |
| Output Capacitance                  | C <sub>oss</sub>    | —   | —   | 25   | pF   |  |
| Reverse Transfer Capacitance        | C <sub>rss</sub>    | —   | —   | 8.0  | pF   |  |
| <b>SWITCHING CHARACTERISTICS</b>    |                     |     |     |      |      |  |
| Turn-On Delay Time                  | t <sub>D(ON)</sub>  | —   | —   | 20   | ns   | V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>GEN</sub> = 50Ω |
| Turn-Off Delay Time                 | t <sub>D(OFF)</sub> | —   | —   | 20   | ns   |  |

- Notes: 6. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes Incorporated's suggested pad layout, which can be found on our website at <http://www.diodes.com/package-outlines.html>.  
7. Short duration pulse test used to minimize self-heating effect.

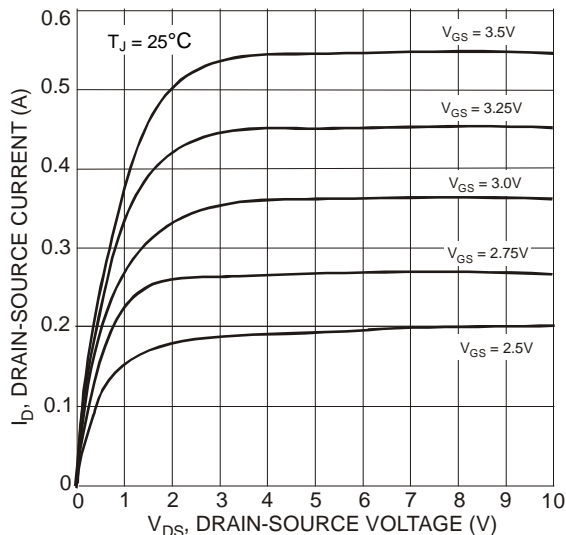


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

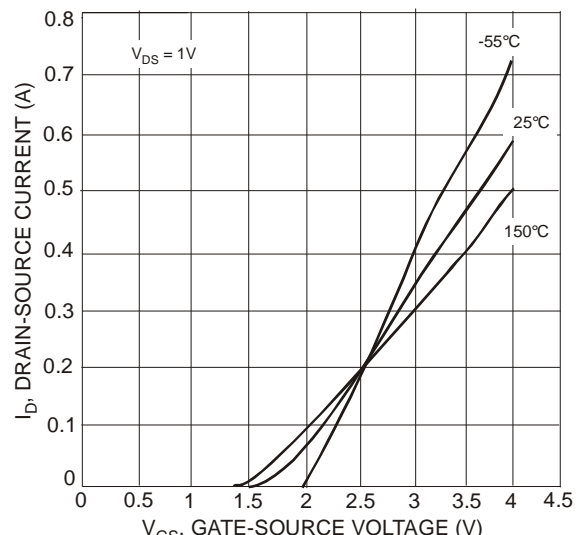


Fig. 2 Transfer Characteristics

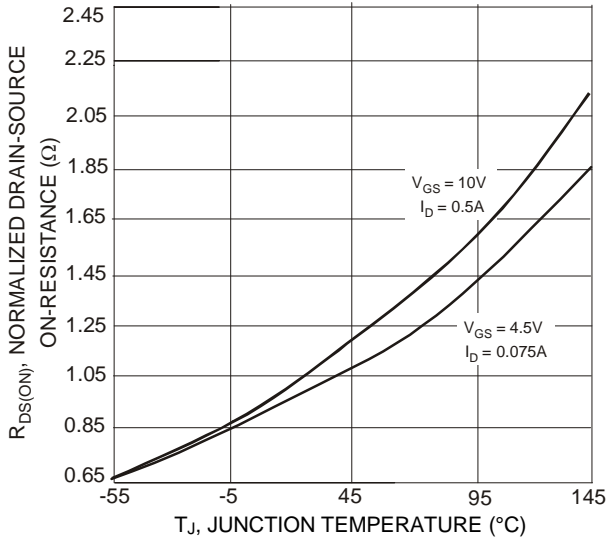


Fig. 3 Drain-Source On-Resistance vs. Junction Temperature

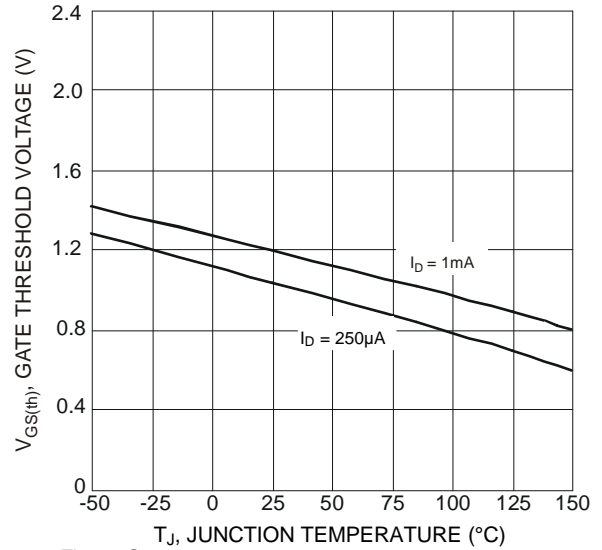


Fig. 4 Gate Threshold Variation vs. Junction Temperature

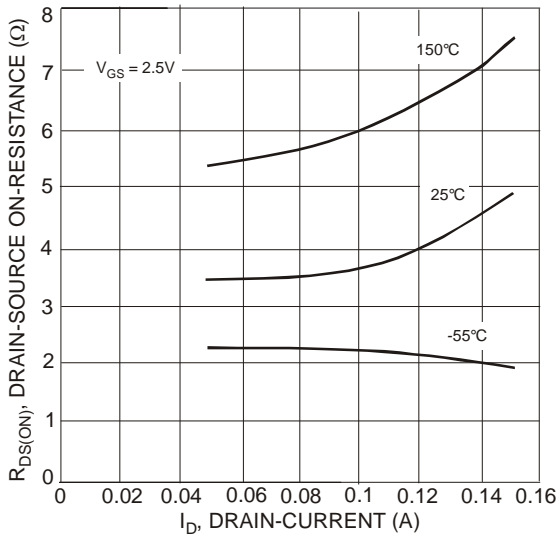


Fig. 5 Drain-Source On-Resistance vs. Drain-Current

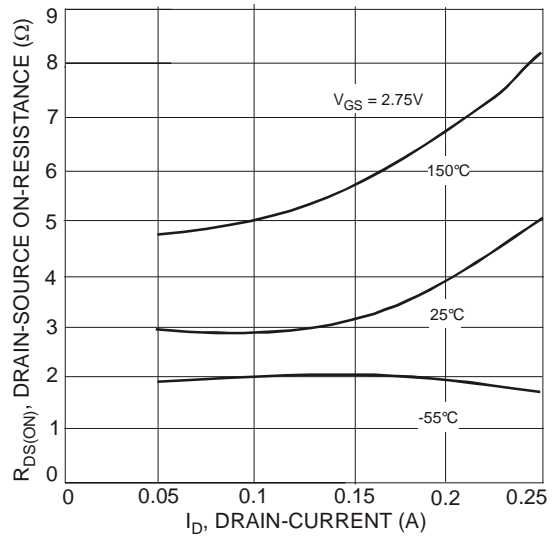


Fig. 6 Drain-Source On-Resistance vs. Drain-Current

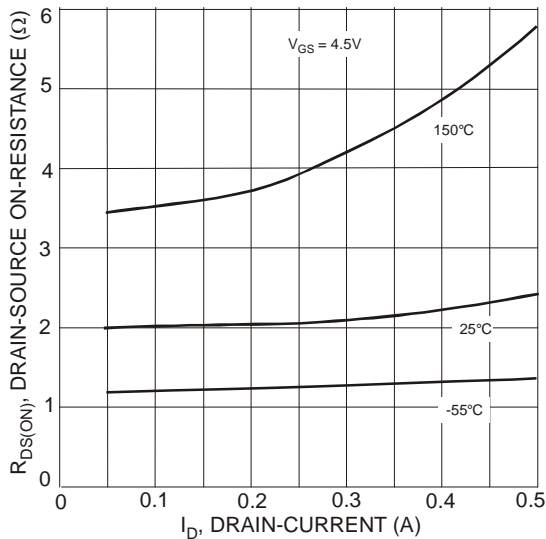


Fig. 7 Drain-Source On-Resistance vs. Drain-Current

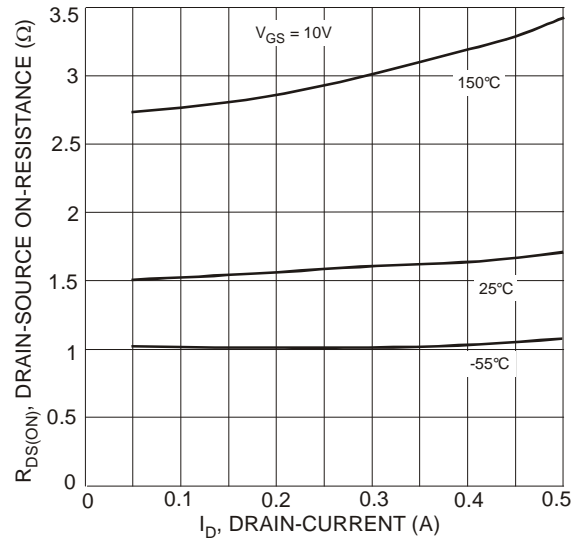


Fig. 8 Drain-Source On Resistance vs. Drain-Current

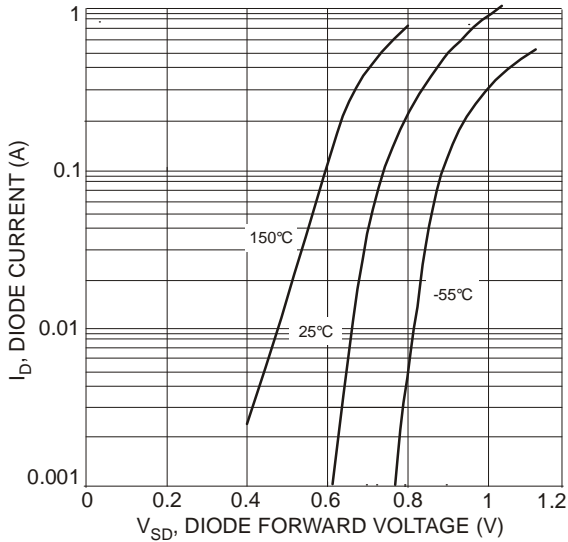


Fig. 9 Body Diode Current vs. Body Diode Voltage

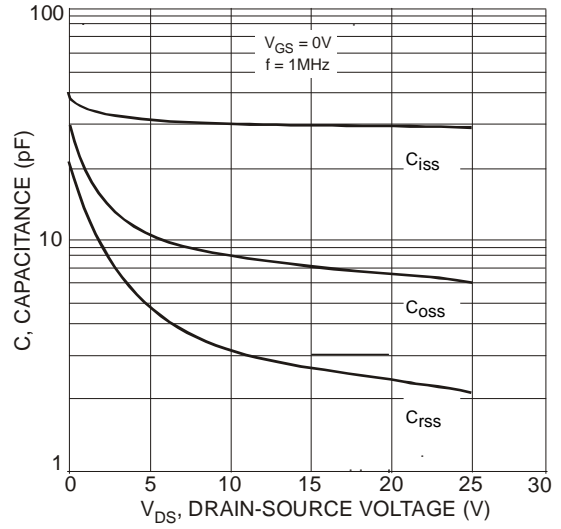
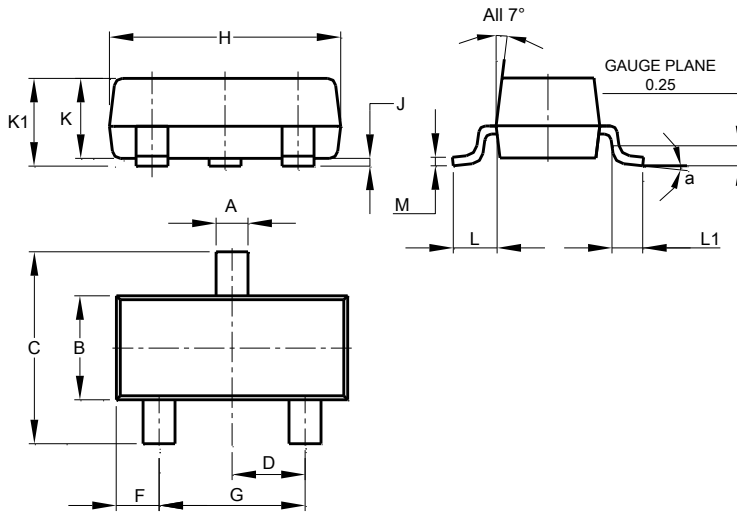


Fig. 10 Capacitance vs. Drain-Source Voltage

## Package Outline Dimensions

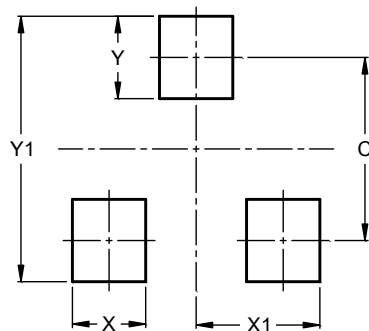
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



| SOT23                |       |       |       |
|----------------------|-------|-------|-------|
| Dim                  | Min   | Max   | Typ   |
| A                    | 0.37  | 0.51  | 0.40  |
| B                    | 1.20  | 1.40  | 1.30  |
| C                    | 2.30  | 2.50  | 2.40  |
| D                    | 0.89  | 1.03  | 0.915 |
| F                    | 0.45  | 0.60  | 0.535 |
| G                    | 1.78  | 2.05  | 1.83  |
| H                    | 2.80  | 3.00  | 2.90  |
| J                    | 0.013 | 0.10  | 0.05  |
| K                    | 0.890 | 1.00  | 0.975 |
| K1                   | 0.903 | 1.10  | 1.025 |
| L                    | 0.45  | 0.61  | 0.55  |
| L1                   | 0.25  | 0.55  | 0.40  |
| M                    | 0.085 | 0.150 | 0.110 |
| a                    | 0°    | 8°    | --    |
| All Dimensions in mm |       |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 2.0           |
| X          | 0.8           |
| X1         | 1.35          |
| Y          | 0.9           |
| Y1         | 2.9           |

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